

Substitute for form 1449/PTO		Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)		Application Number	10/802,186-Conf. #3869
		Filing Date	March 17, 2004
		First Named Inventor	Cheng
		Art Unit	2811
		Examiner Name	Shouxiang Hu
Sheet	1	of	3
		Attorney Docket Number	ASC-025DV2C1

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Examiner Initials*	Cite No. ¹	Document Number Number-Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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		Country Code ² -Number ³ -Kind Code ² (if known)					
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	B53	JP-6-252046		09-09-1994		Abstract only	✓
	B54	JP-61-141116		06-28-1986		Abstract only	✓

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NON PATENT LITERATURE DOCUMENTS			
Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
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